

# CMS35P06D-HF

**P-Channel**  
**RoHS Device**  
**Halogen Free**



## Features

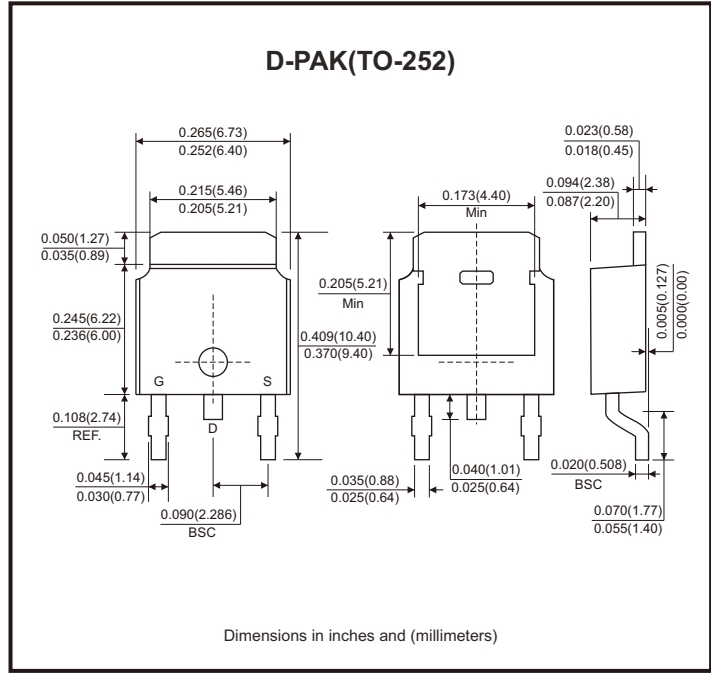
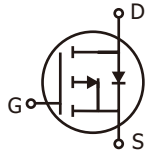
- Advanced DMOS trench technology.
- Fast switching.
- Green device available.
- 100% EAS guaranteed.

## Mechanical data

- Case: D-PAK(TO-252) standard package, molded plastic.

## Circuit Diagram

- G : Gate
- S : Source
- D : Drain



## Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
Drain-source voltage		$V_{DS}$	-60	V
Gate-source voltage		$V_{GS}$	±20	V
Continuous drain current (Note 1)	$I_D @ T_C = 25^\circ C$		-35	A
	$I_D @ T_C = 100^\circ C$		-22.1	
Pulsed drain current (Note 1, 2)		$I_{DM}$	-140	A
Total power dissipation (Note 4)	$P_D @ T_C = 25^\circ C$		72.6	W
	$P_D @ T_A = 25^\circ C$		2	
Single pulse avalanche energy, L=0.1mH (Note 3)		$E_{AS}$	80	mJ
Single pulse avalanche current, L=0.1mH (Note 3)		$I_{AS}$	-40	A
Operating junction and storage temperature range		$T_J, T_{STG}$	-55 to +150	°C
Thermal resistance junction-ambient (Note 1)	Steady state	$R_{\theta JA}$	62.5	°C/W
Thermal resistance junction-case (Note 1)	Steady state	$R_{\theta JC}$	1.72	°C/W

## Electrical Characteristics (at T<sub>j</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-60			V
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.4	-2.5	
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V			±100	nA
Drain-source leakage current (T <sub>j</sub> =25°C)	I <sub>DSS</sub>	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V			-1	μA
Drain-source leakage current (T <sub>j</sub> =125°C)		V <sub>DS</sub> = -48V, V <sub>GS</sub> = 0V			-10	
Static drain-source on-resistance (Note 2)	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -20A		23	28	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A		28	35	
Total gate charge (Note 2)	Q <sub>g</sub>	I <sub>D</sub> = -5A, V <sub>DS</sub> = -30V, V <sub>GS</sub> = -10V		43.8		nC
Gate-source charge	Q <sub>gs</sub>			4.6		
Gate-drain ("miller") charge	Q <sub>gd</sub>			8.3		
Turn-on delay time (Note 2)	t <sub>d(on)</sub>	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V I <sub>D</sub> = -1A, R <sub>G</sub> = 6Ω		25		nS
Rise time	t <sub>r</sub>			13.8		
Turn-off delay time	t <sub>d(off)</sub>			148		
Fall time	t <sub>f</sub>			51		
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -25V, f = 1MHz		2595		pF
Output capacitance	C <sub>oss</sub>			162		
Reverse transfer capacitance	C <sub>rss</sub>			115		
<b>Source-drain diode</b>						
Diode forward voltage (Note 2)	V <sub>SD</sub>	I <sub>S</sub> = -20A, V <sub>GS</sub> = 0V, T <sub>J</sub> =25°C			-1.2	V
Continuous source current (Note 1, 6)	I <sub>S</sub>	V <sub>G</sub> = V <sub>D</sub> = 0V, Force current			-35	A
Pulsed source current (Note 2, 6)	I <sub>SM</sub>				-70	A
<b>Guaranteed avalanche characteristics</b>						
Single pulse avalanche energy (Note 5)	EAS	V <sub>DD</sub> = -25V, L=0.1mH, I <sub>AS</sub> = -20A	20			mJ

- Notes: 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2 oz copper.  
 2. The data tested by pulsed, pulse width ≤300μs, duty cycle ≤ 2%.  
 3. The EAS data shows max. rating. The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.1mH, I<sub>AS</sub>=-40A.  
 4. The power dissipation is limited by 150°C junction temperature.  
 5. The min. value is 100% EAS tested guarantee.  
 6. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

## Rating and Characteristic Curves (CMS35P06D-HF)

Fig.1 - Drain Current vs.  $T_c$

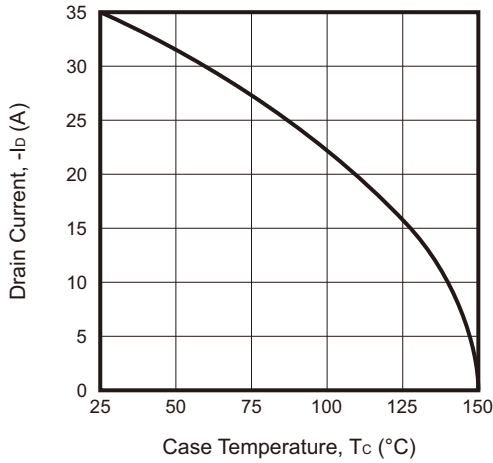


Fig.2 - Gate Charge Characteristics

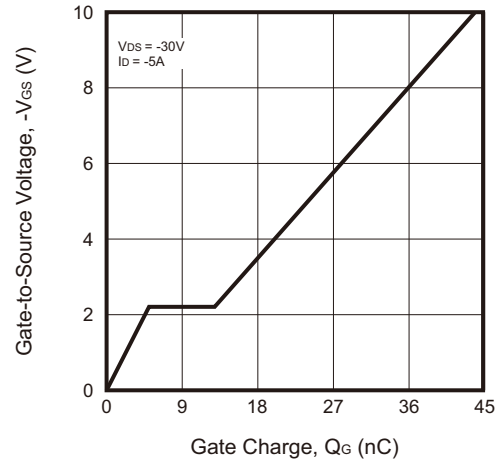


Fig.3 - Normalized  $V_{GS(th)}$  vs.  $T_J$

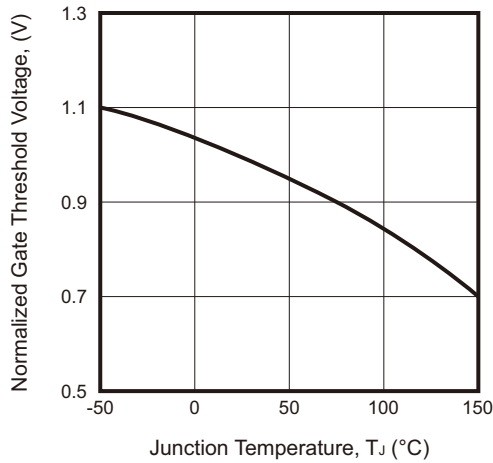


Fig.4 - Normalized  $R_{DS(on)}$  vs.  $T_J$

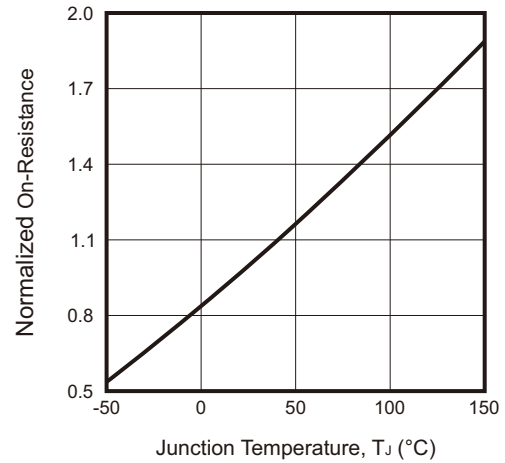
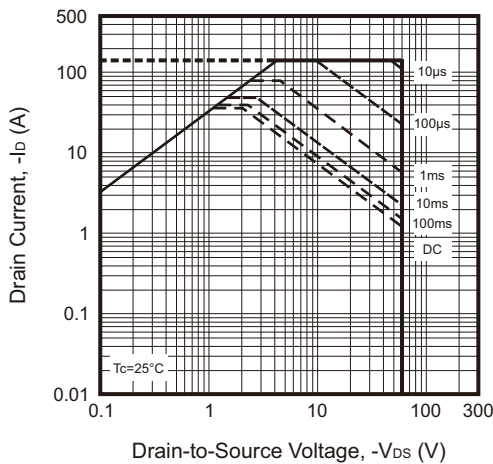
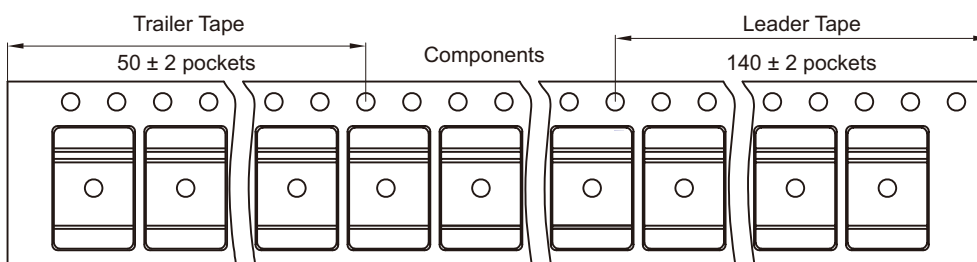
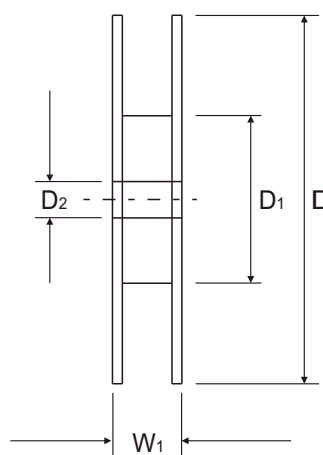
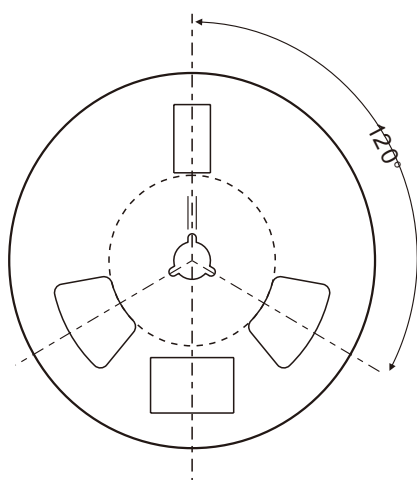
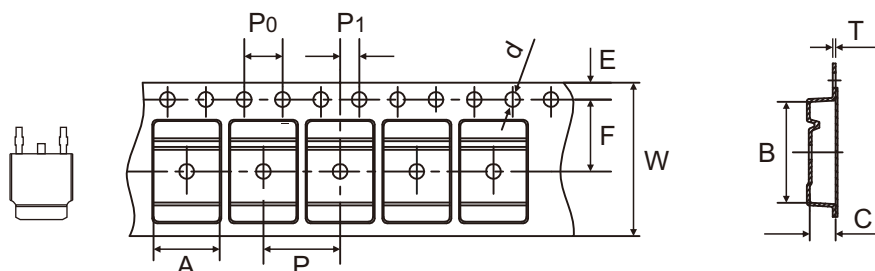


Fig.5 - Safe Operating Area



## Reel Taping Specification



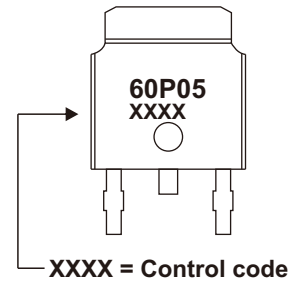
TO-252 (D-PAK)	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.90 ± 0.10	10.50 ± 0.10	2.70 ± 0.10	1.55 ± 0.05	332 Max	100.00 ± 2.00	13.00 Min
	(inch)	0.272 ± 0.004	0.413 ± 0.004	0.106 ± 0.004	0.061 ± 0.002	13.071 Max	3.937 ± 0.079	0.512 Min

TO-252 (D-PAK)	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	7.50 ± 0.10	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.30 ± 0.05	16.00 ± 0.10	22.4 Max
	(inch)	0.069 ± 0.004	0.295 ± 0.004	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.012 ± 0.002	0.630 ± 0.004	0.882 Max

Company reserves the right to improve product design, functions and reliability without notice. REV:A

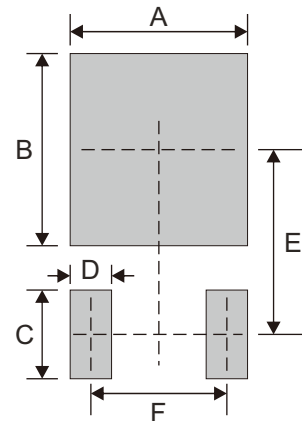
## Marking Code

Part Number	Marking Code
CMS35P06D-HF	60P05



## Suggested PAD Layout

SIZE	TO-252/D-PAK	
	(mm)	(inch)
A	6.00	0.236
B	6.50	0.256
C	3.00	0.118
D	1.40	0.055
E	6.25	0.246
F	4.60	0.181



Note: 1. The pad layout is for reference purposes only.

## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
TO-252/D-PAK	3,000	13